

## Request For Quotation

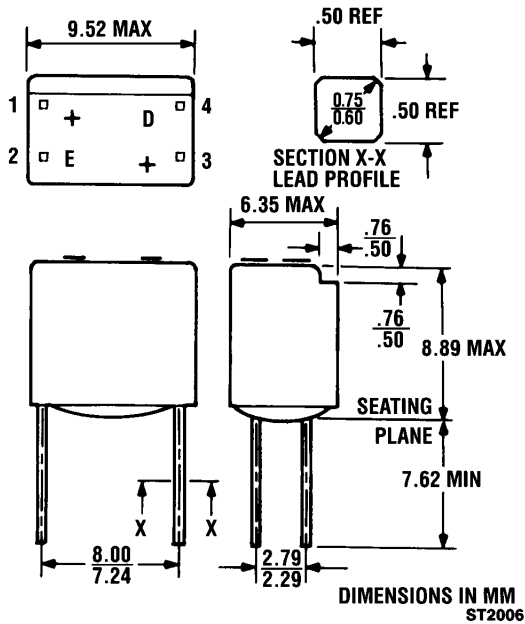
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**PACKAGE DIMENSIONS**

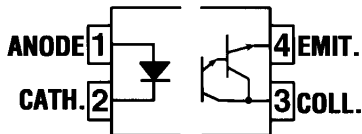


**DESCRIPTION**

The H24B series consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor. The devices are housed in a low-cost plastic package with lead spacing compatible with a dual in-line package.

**FEATURES**

- 4-pin configuration
- Small package size and low cost
- UL recognized-file E51868
- High current transfer ratio



ST4004

*Equivalent Circuit*

**ABSOLUTE MAXIMUM RATINGS**

**TOTAL PACKAGE**

Storage temperature . . . . . -55°C to 85°C  
 Operating temperature . . . . . -55°C to 85°C  
 Lead solder temperature . . . . . 260°C for 5 sec

**INPUT DIODE**

Power dissipation (25°C ambient) . . . . . 100 mW  
 Derate linearly (above 25°C) . . . . . 1.67 mW/°C  
 Continuous forward current . . . . . 60 mA  
 Peak forward current (1 μs pulse, 300pps) . . . . . 3 A  
 Reverse voltage . . . . . 4 V

**DETECTOR**

Power dissipation (at 25°C ambient) . . . . . 150 mW  
 Derate linearly (above 25°C ambient) . . . . . 2.5 mW/°C  
 V<sub>CEO</sub> . . . . . 30 V  
 V<sub>ECC</sub> . . . . . 7 V  
 Continuous forward current . . . . . 100 mA